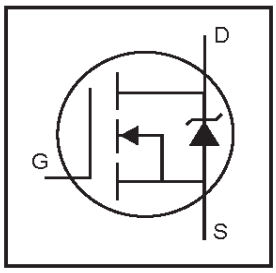
PD - 95600A

IRFR/U1205PbF

HEXFET® Power MOSFET

- Ultra Low On-Resistance
- Surface Mount (IRFR1205)
- Straight Lead (IRFU1205)
- Fast Switching
- Fully Avalanche Rated
- Lead-Free



V_{DSS} = 55V

$R_{DS(on)}$ = 0.027Ω

I_D = 44A⑤

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

The D-PAK is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.

D-Pak
IRFR22ON

I-Pak
IRFU220N

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	44⑤	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	31⑤	
I_{DM}	Pulsed Drain Current ①⑦	160	
P_D @T_C = 25°C	Power Dissipation	107	W
	Linear Derating Factor	0.71	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy②⑦	210	mJ
I_{AR}	Avalanche Current①⑦	25	A
E_{AR}	Repetitive Avalanche Energy①⑦	11	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	–—	1.4	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount) **	–—	50	
$R_{\theta JA}$	Junction-to-Ambient	–—	110	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.055	—	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.027	Ω	V_{GS} = 10V, I_D = 26A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 250µA
g_{fs}	Forward Transconductance	17	—	—	S	V_{DS} = 25V, I_D = 25A⑦
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	µA	V_{DS} = 55V, V_{GS} = 0V
		—	—	250		V_{DS} = 44V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V_{GS} = -20V
Q_g	Total Gate Charge	—	—	65	nC	I_D = 25A
Q_{gs}	Gate-to-Source Charge	—	—	12		V_{DS} = 44V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	27		V_{GS} = 10V, See Fig. 6 and 13 ④⑦
$t_{d(on)}$	Turn-On Delay Time	—	7.3	—	ns	V_{DD} = 28V
t_r	Rise Time	—	69	—		I_D = 25A
$t_{d(off)}$	Turn-Off Delay Time	—	47	—		R_G = 12Ω
t_f	Fall Time		60			R_D = 1.1Ω, See Fig. 10 ④⑦
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact⑥
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	1300	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	410	—		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	—	150	—		f = 1.0MHz, See Fig. 5⑦

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	44⑤	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①⑦	—	—	160		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	T_J = 25°C, I_S = 22A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	—	65	98	ns	T_J = 25°C, I_F =25A
Q_{rr}	Reverse RecoveryCharge	—	160	240	nC	di/dt = 100A/µs ④⑦
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② V_{DD} = 25V, starting T_J = 25°C, L = 470µH R_G = 25Ω, I_{AS} = 25A. (See Figure 12)

③ I_{SD} ≤ 25A, di/dt ≤ 320A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 175°C

④ Pulse width ≤ 300µs; duty cycle ≤ 2%.

⑤ Calculated continuous current based on maximum allowable junction temperature; Package limitation current = 20A

⑥ This is applied for I-PAK, Ls of D-PAK is measured between lead and center of die contact

⑦ Uses IRFZ44N data and test conditions

** When mounted on 1" square PCB (FR-4 or G-10 Material) .
For recommended footprint and soldering techniques refer to application note #AN-994

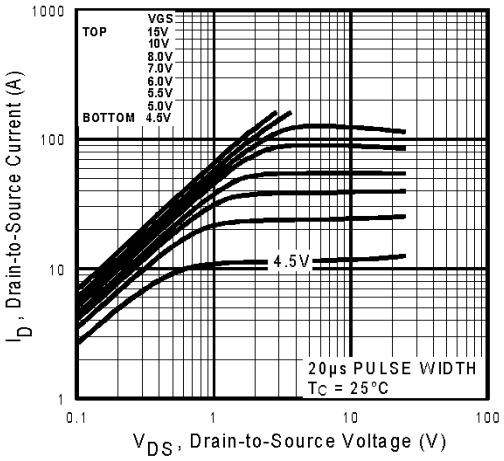


Fig 1. Typical Output Characteristics

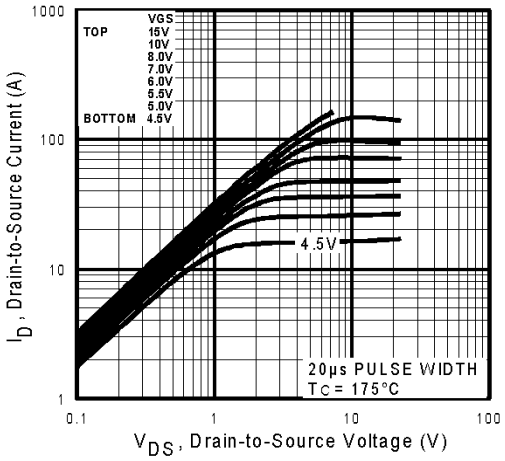


Fig 2. Typical Output Characteristics

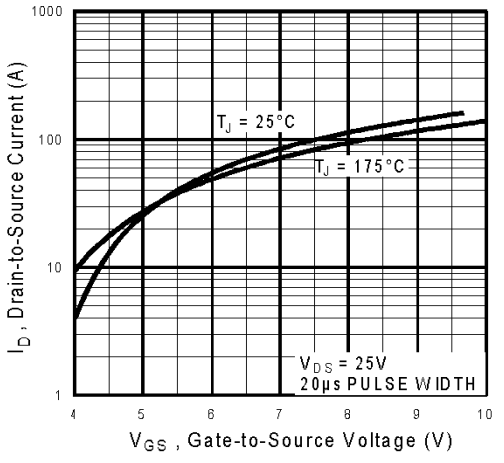


Fig 3. Typical Transfer Characteristics

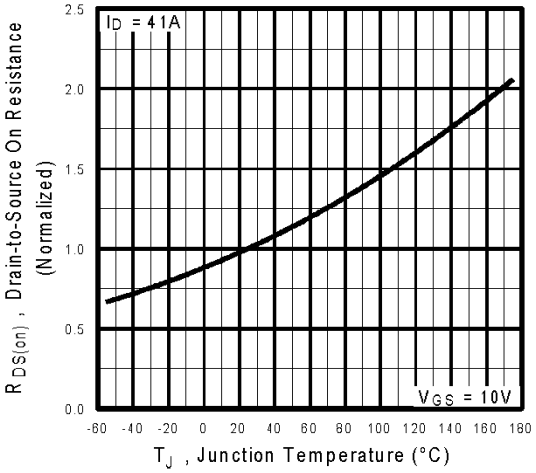


Fig 4. Normalized On-Resistance Vs. Temperature